Wire Bond Introduction



Contents



- Wire Bond Sequence
- Wire Bond Introduction
- Wire Bond Process
- Quality

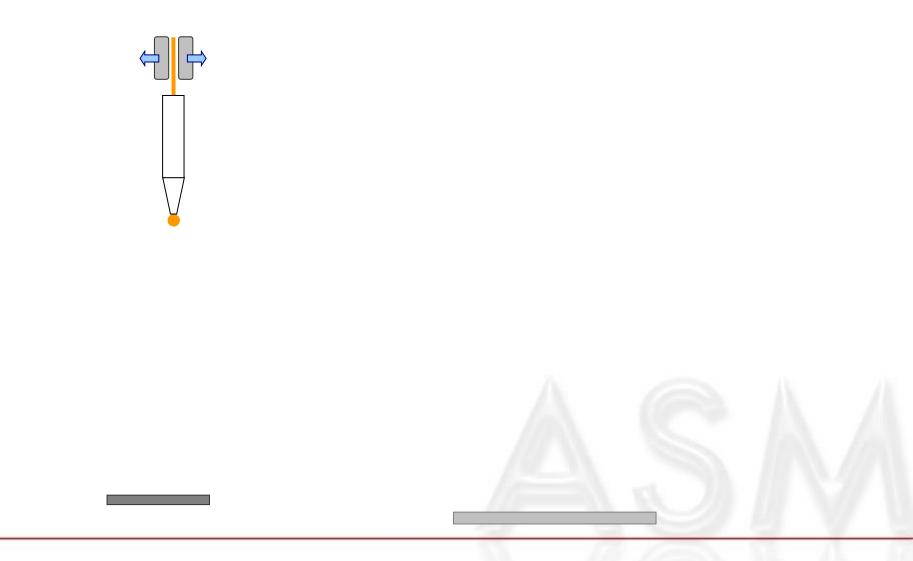
















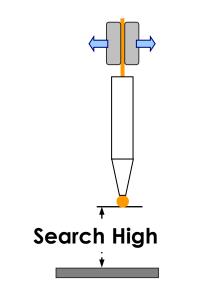




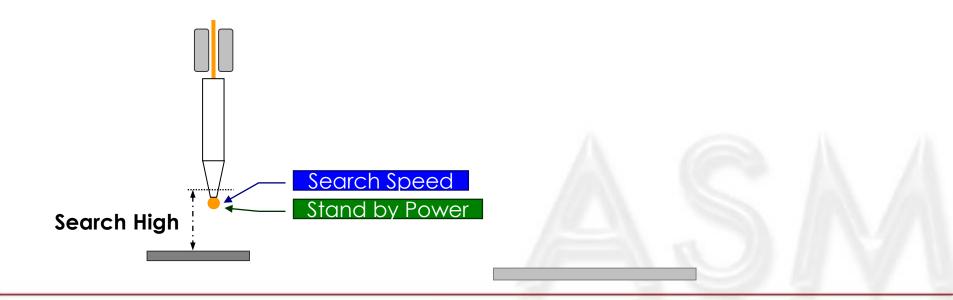




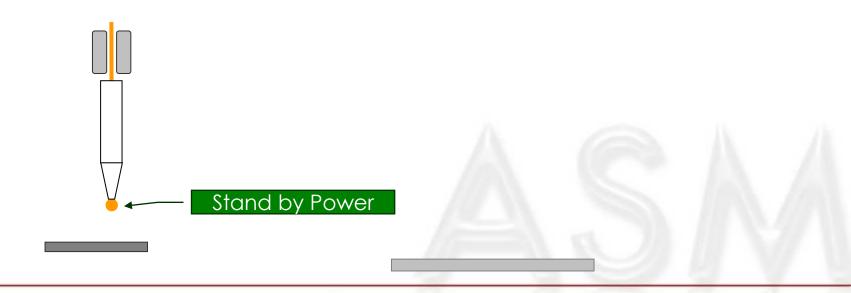








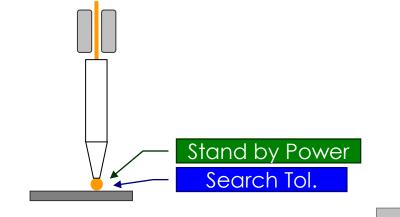




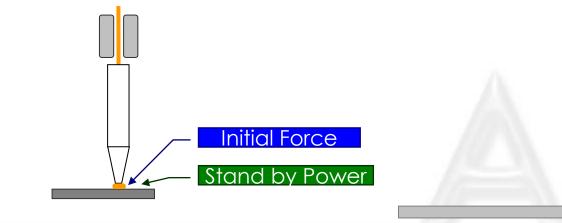




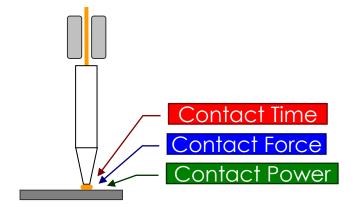






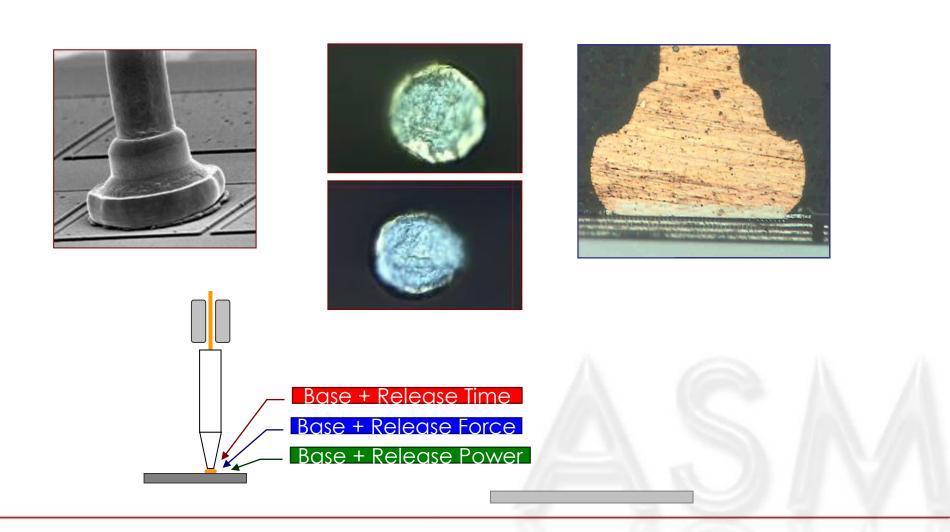




















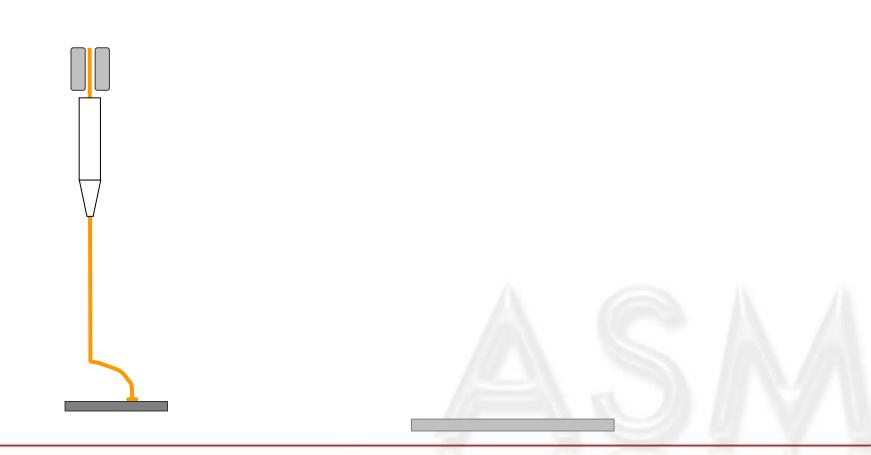




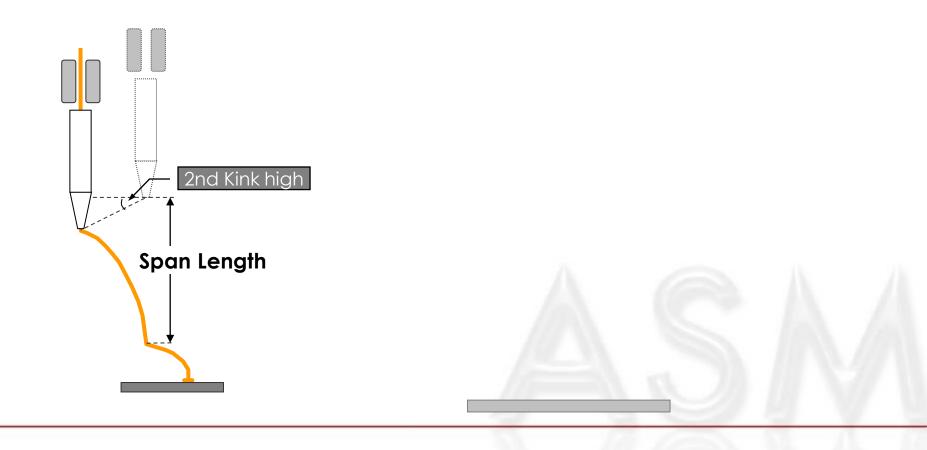










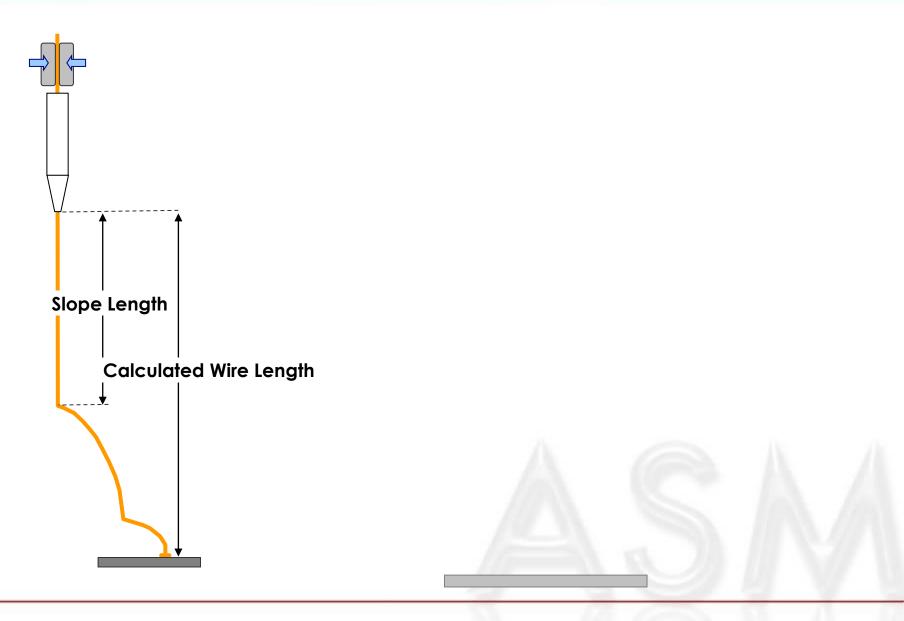












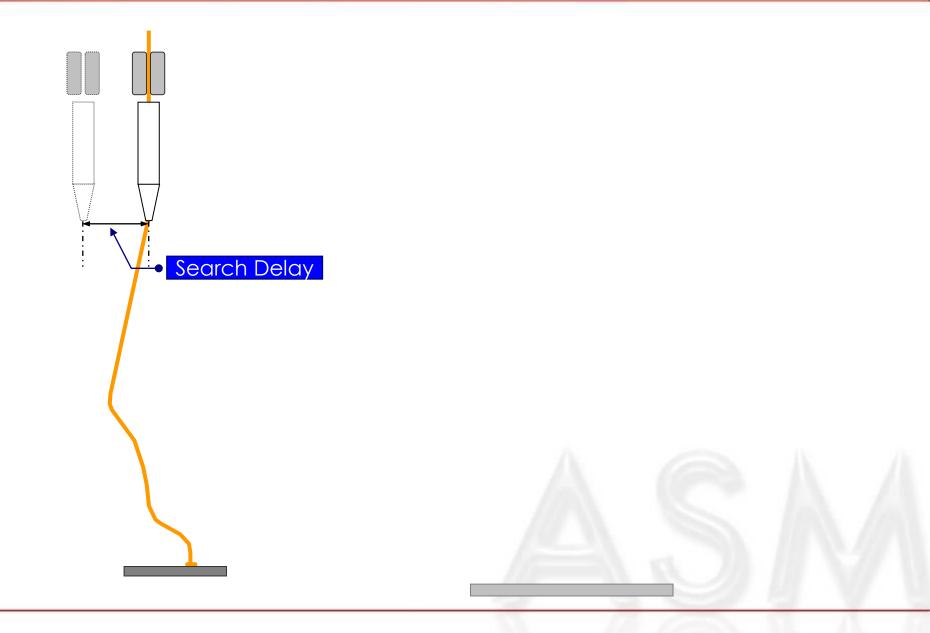
ASM

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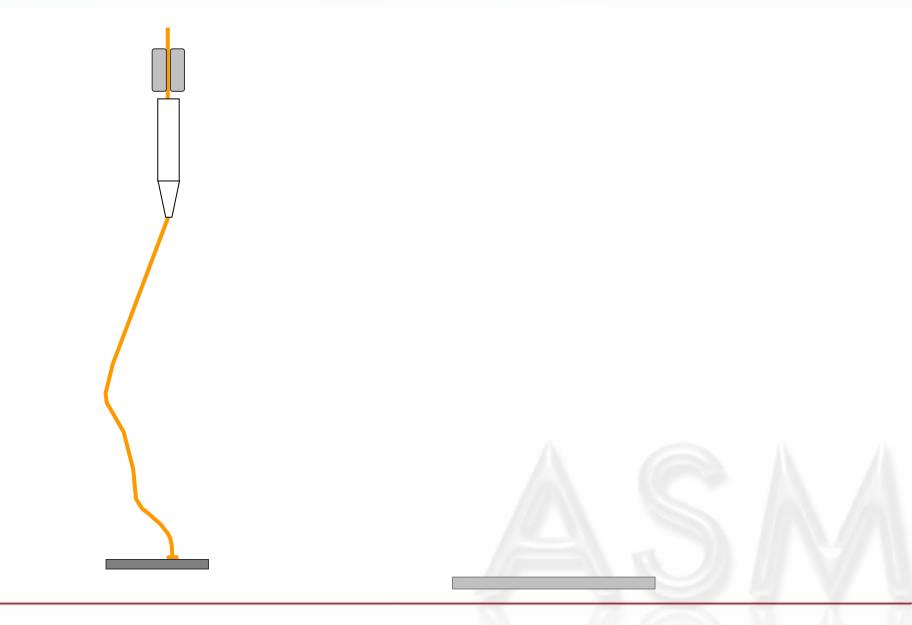




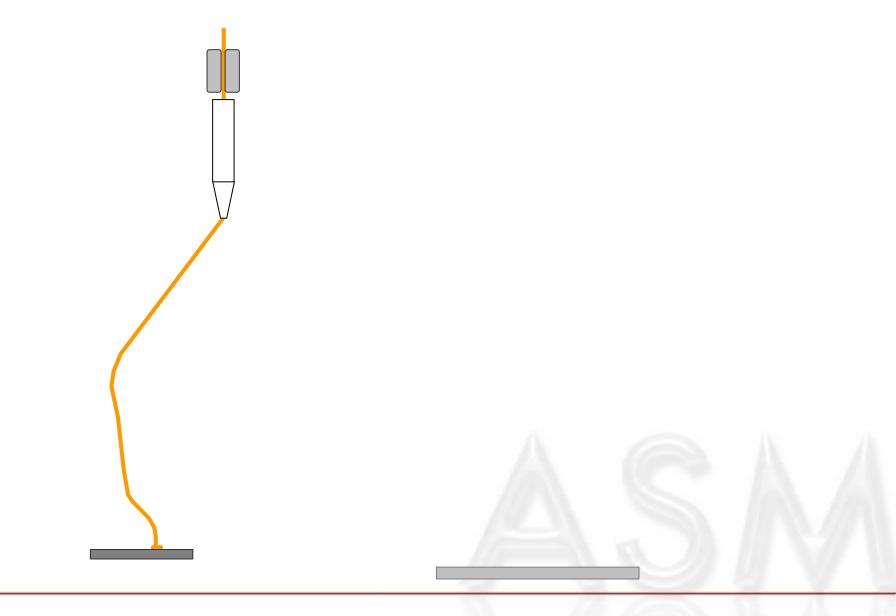




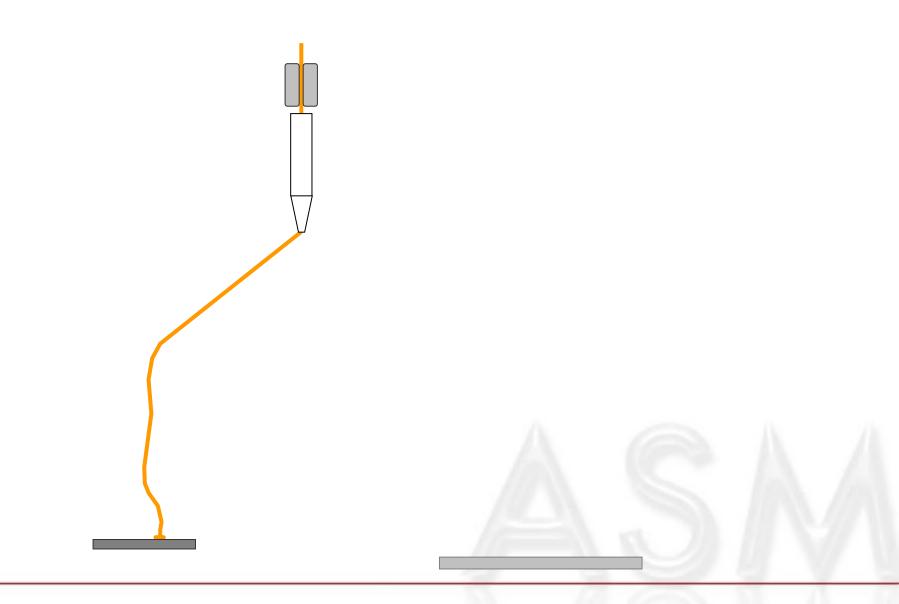




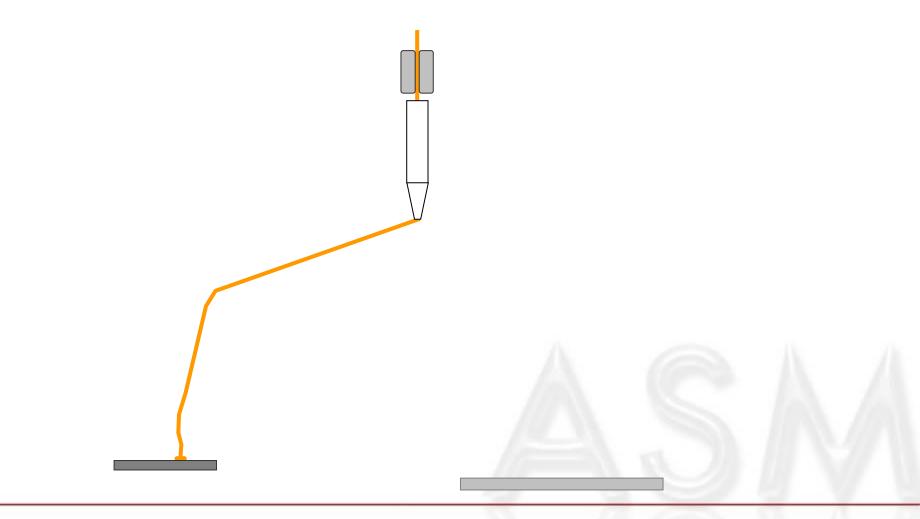




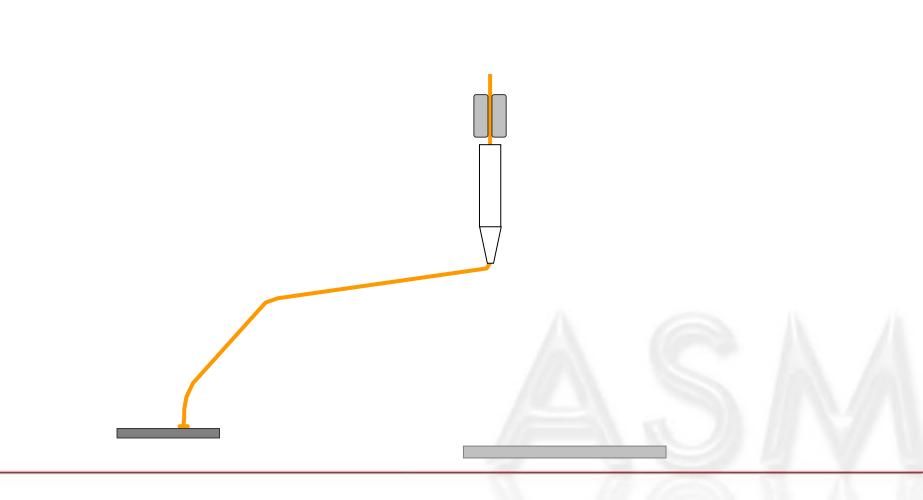




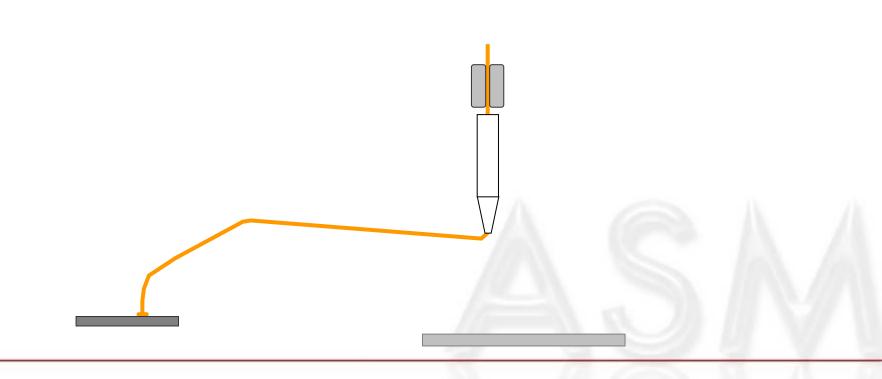




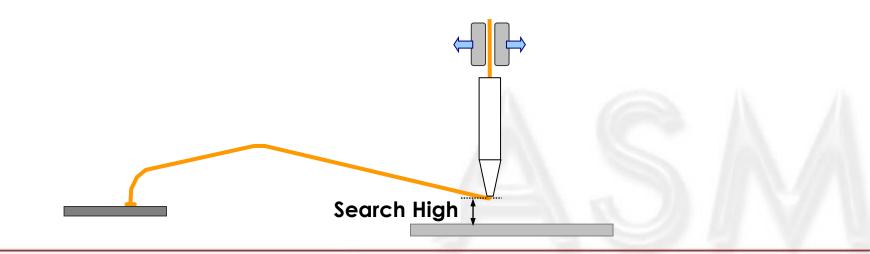




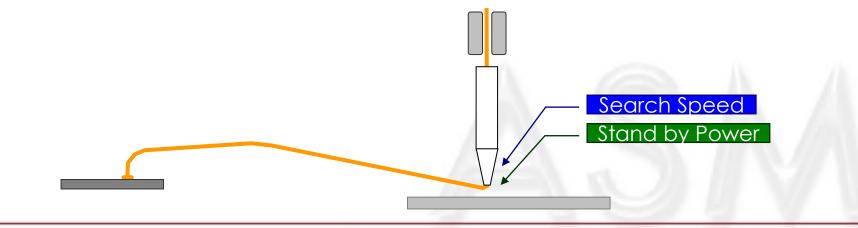




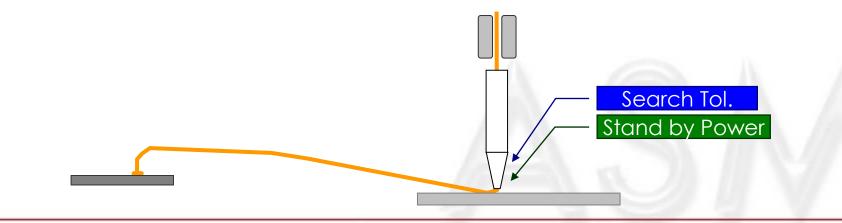




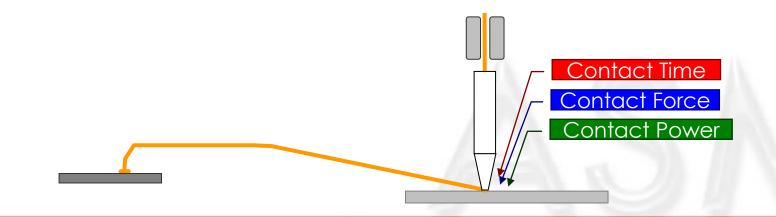




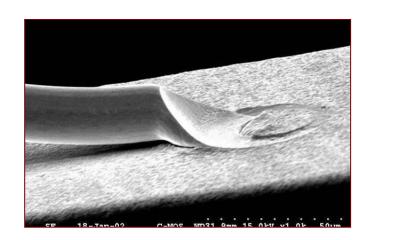






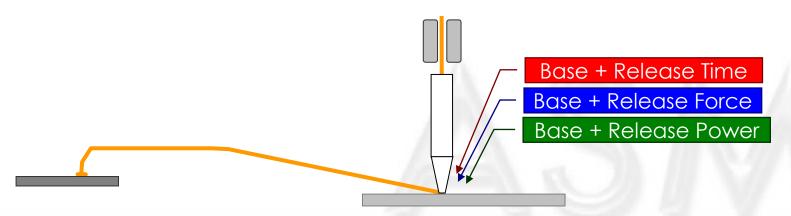




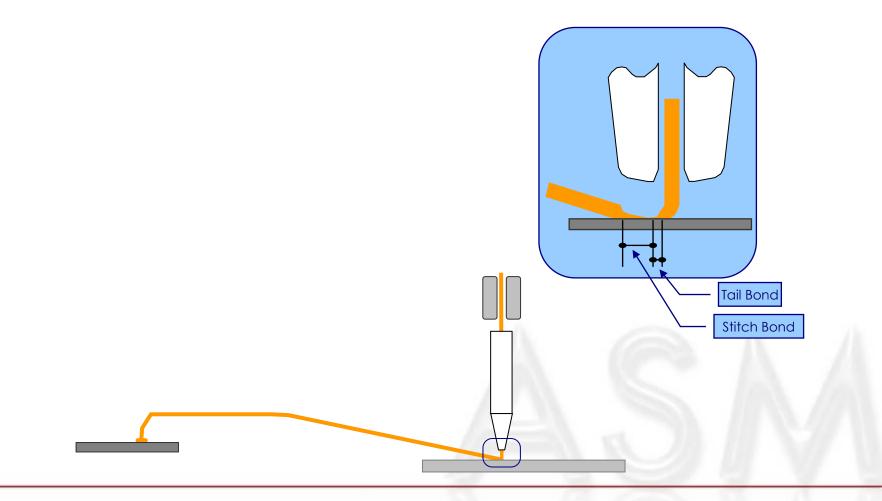




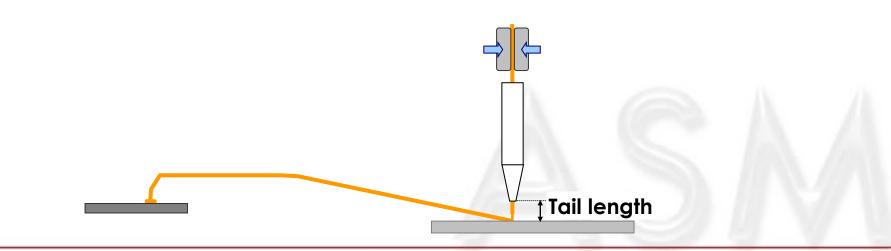




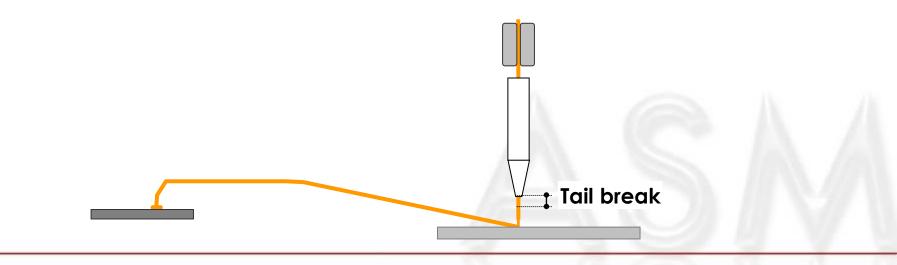




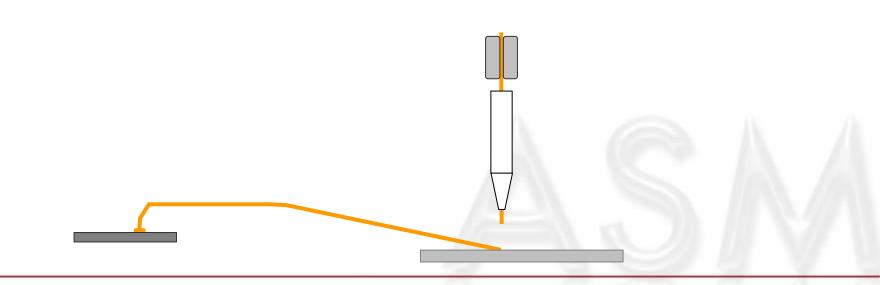




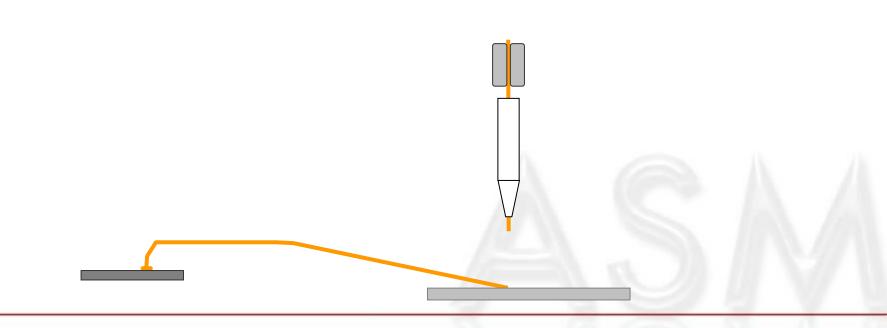




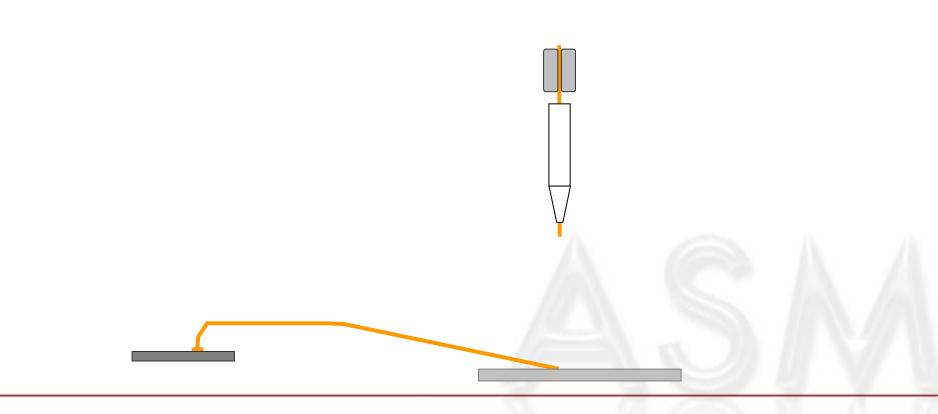




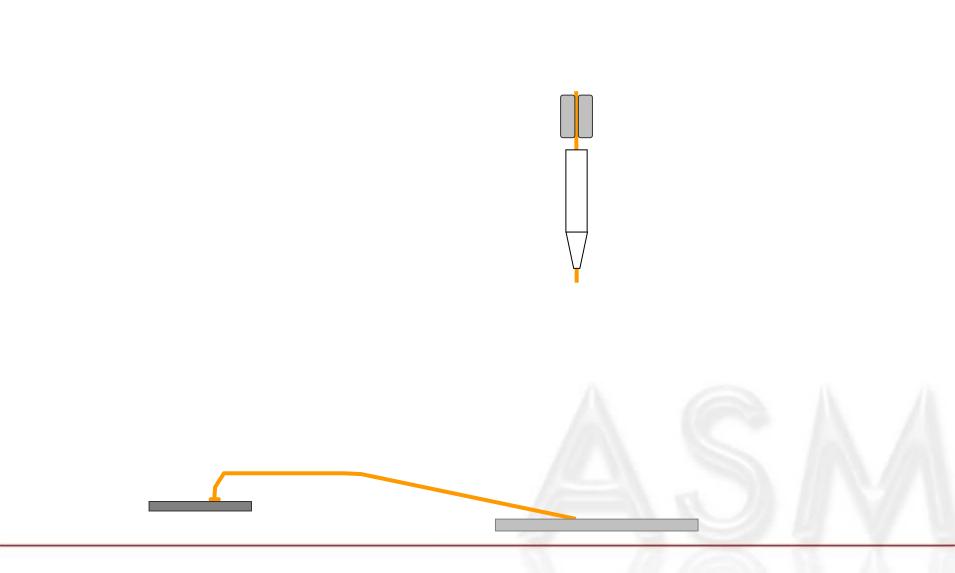




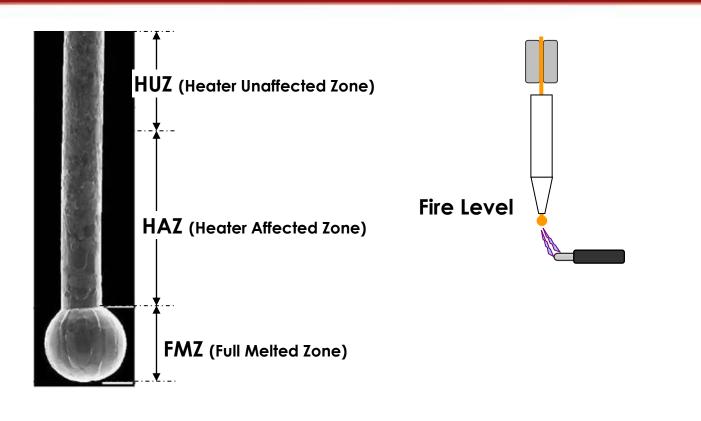


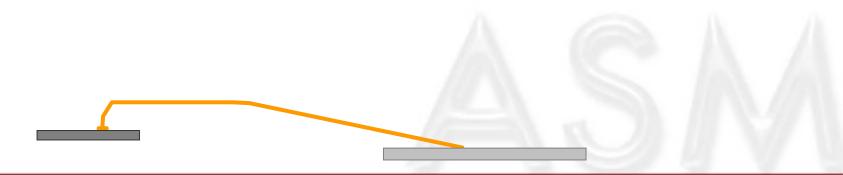








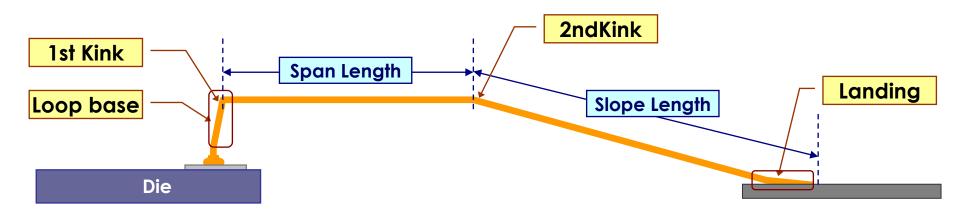


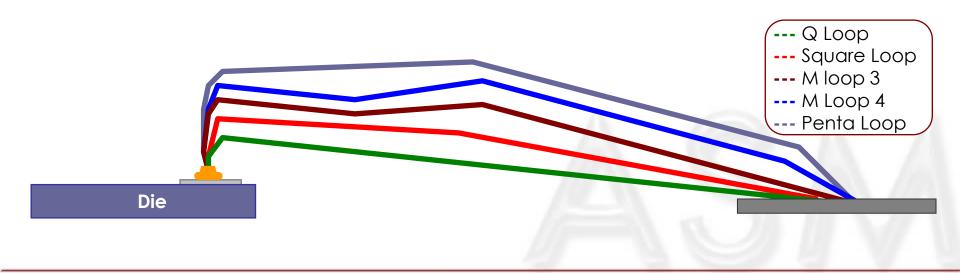


Wire Bond (Looping)



Follow bonding





Wire Bond (Loop Mode)



□ Q_loop

- WL: 0.05mm~1.7mm
- High bonding speed
- Looping strength is low

Penta loop

- WL: 1.5mm~5.5mm
- Looping strength is middle
- To avoid landing touch finger (Lead)
- Span length over 70~85%

M_loop 3

- WL: 1.5mm~5.5mm
- Looping strength is high
- To provide stronger support on span length
- Low loop with long wire
 - 100um loop high with
 3.5mm WL

Square loop

- WL: 0.8mm~3.5mm
- Looping strength is middle
- To avoid touch die edge
- Span length over 70% is limitation

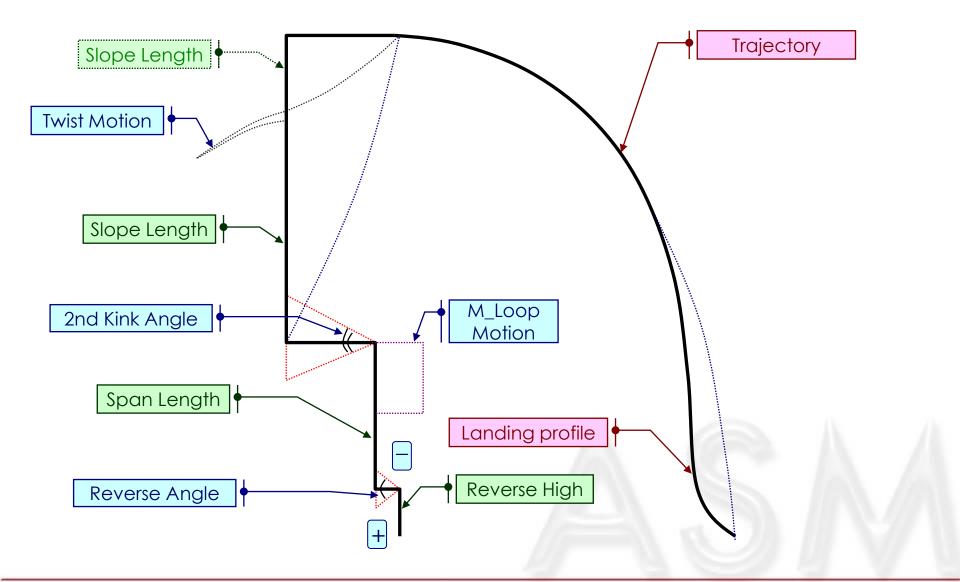
• Condition for WL is 0.8mil WD with 200umm loop high

M_loop 4

- WL: 1.5mm~5.5mm
- Looping strength is high
- To provide stronger support on span & slope length
- Low loop with long wire
 - 120um loop high with
 4.2mm WL

Wire Bond (Loop Profile)





Wire Bond (Bonding Mode)





- 1st bond level is higher than (the same as) 2nd bond
 - Normal bonding
 - It is general bonding mode on wire bond
 - » From die to finger
 - BSOB (Bond Stitch On Ball) Bonding
 - To cover finger contamination issue
 - Major application is for QFN with tape
 - Die to Die application





Wire Bond (Bonding Mode)









Reverse Bonding

- Ist bond level is lower than 2nd bond
 - Normal bonding
 - Form die to lead/ from GND to lead
 - BSOB (Bond Stitch On Ball) Bonding
- From GND (lead) to Die

BBOS (Bond Ball On Stitch)

- Enhance stitch pull
- Reduce the risk to cause wire sweep/ NSOL/ short tail
 - Due to the platform of standoff ball is unevenness

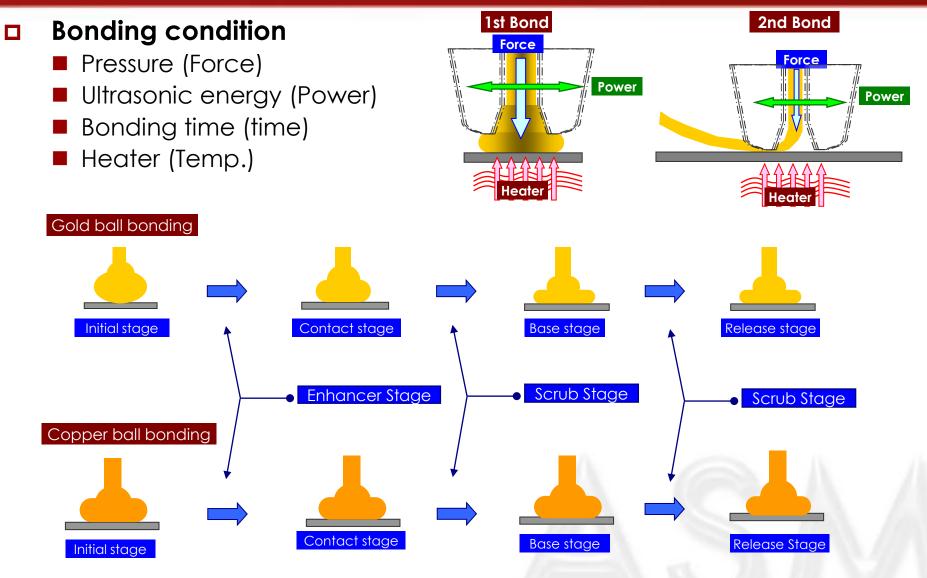
BSOS (Bond Stitch On Stitch)

- Enhance stitch pull
- Reduce wire usage amount



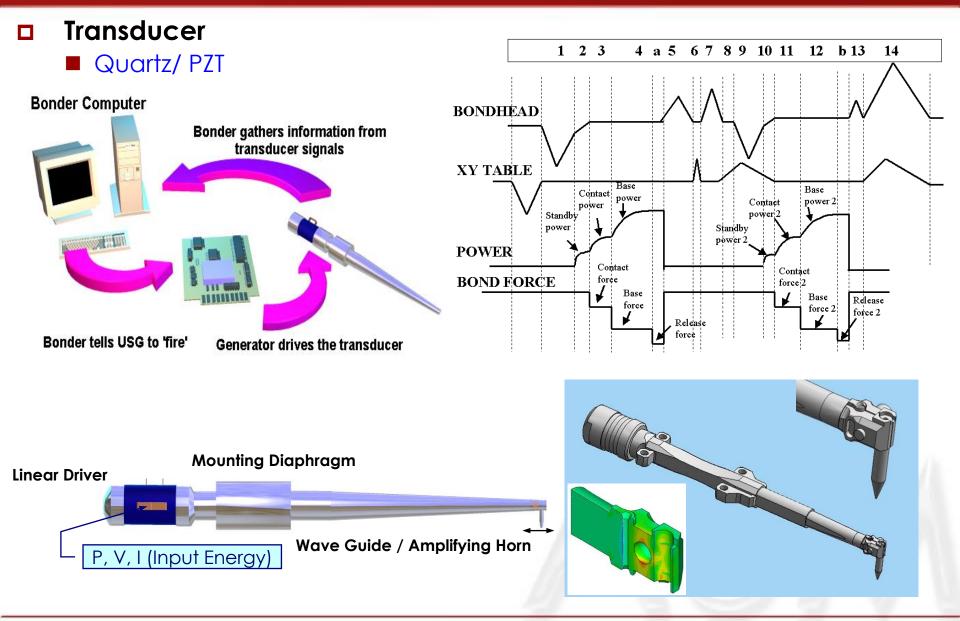
Bonding





Bonding (Ultrasonic)

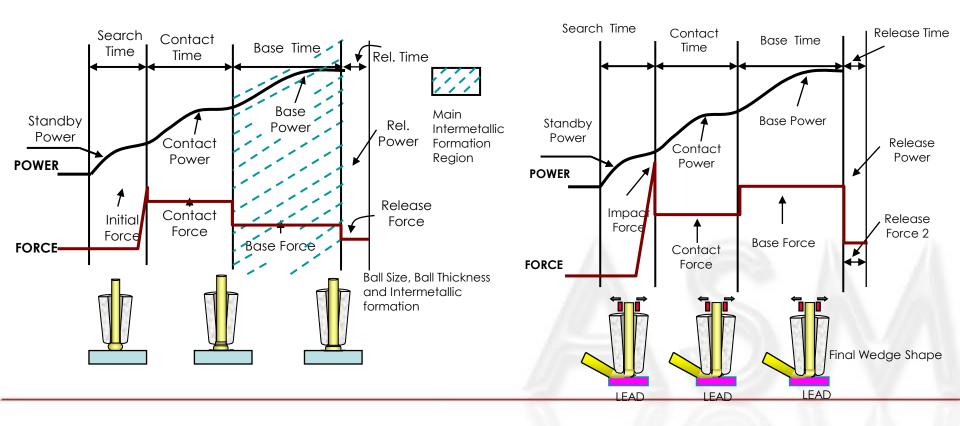




Bonding (Ultrasonic)

Application & Capability

- Best flexibility for difference application
- Provide "Real Time" Bond Quality Monitoring (BQM)
- Selectable for 1st and 2nd bond
- Provide multiple control modes
 - Constant Voltage/Current/Power mode





Ultrasonic (Control Mode)



C_I (Constant Current)

 \square P = (I^2)*R, when "I" = constant

Impedance "Z" increase so output power "P" increase to maintain the <u>C</u>onstant current <u>I</u>

C_V (Constant Voltage)

 \square P = I*V and I = V/Z, so P = V^2/Z, when "V" = constant

Impedance "Z" increase so output power "P" decrease to maintain the <u>C</u>onstant <u>V</u>oltage

C_P (Constant Power)

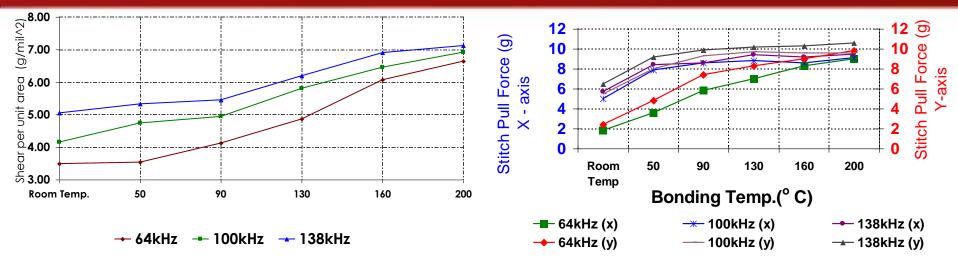
 \square P = I*V and I = V/Z, so P = V^2/Z, when "P" = constant

Impedance "Z" increase so voltage "V" increase to maintain the <u>C</u>onstant <u>P</u>ower

Rise Time Is the time to reach the max power output If the rise time set to 8 ms and base time is 6ms, the power will never reach max value



Ultrasonic (Frequency)



	138kHz	121kHz	64kHz
Room Temp.	138 kHz Transducer 59 degree colclus		64kHz TERP. SP dog C
200deg	138 HE Transfuor		

Bonding (Inter-Metallic Compound)



Au

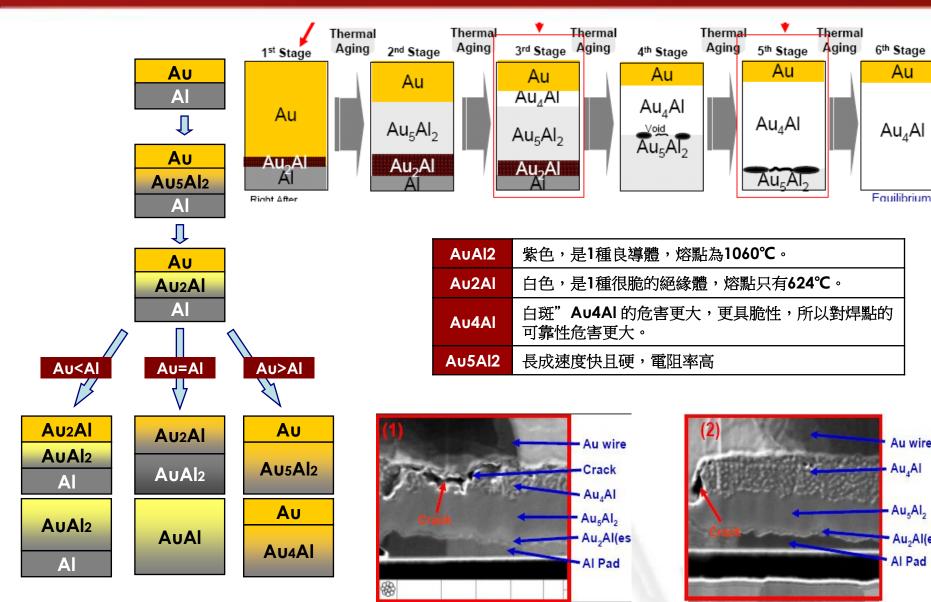
Au wire

Au,Al

Au Al

Al Pad

Au₂Al(est



Bonding (Inter-Metallic Compound)



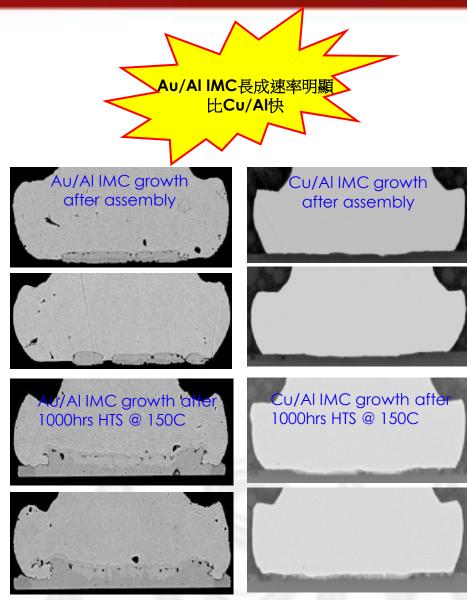
Au/Al vs Cu/Al IMC growth rate comparison.

- 電負度Cu(1.9)和Al(1.6)差別小,而電 負度Au(2.5)和Al(1.6)差別大,電負度 差別越大反應力就越大,所以金和鋁的 反應力大於銅與鋁
 - 電負度又稱陰電性,為判斷原子拉 電子的強度大小
 - □ 常用的元素電負度大小
 - F(4)>O(3.5)>N,CI(3.0)>Br(2.8)>I(2.6) >C,S(2.5)>H(1)

Temperature (deg C)	Cu/Al, K (cm ² /s)	Au/Al, K (cm ²/s)
150	1.878 x 10 ⁻¹⁶	1.1 x 10 ⁻¹⁴
280	2.645 x 10 ⁻¹³	2.4 x 10 ⁻¹¹
350	3.747 x 10 ⁻¹²	3.9 x 10 ⁻¹⁰

"X" is the intermetallic layer thick

"t" is the time



Bonding (Plasma Process)



Plasma Mode

- DC (Direct current)Balzers
- RF (Radio Frequency)
 March, E&R
- MW (Microwave)
 Tepla

Gas process

- H·+ Metal O → Metal + O2 (還原)
 - Weak bombardment effect
- O·+ Metal → Metal O -- (氧化)
 - Moderate bombardment effect
- Ar+ → high energy ions- (撞撃)
 - Strong bombardment effect

	L/F base	Chip contamination	Substrate base	Substrate contamination	
Plasma	March (RF)	E&R (RF)	E&R (RF)	E&R (RF)	
Туре	March (Kr)	March (RF)	Balzers		
Gas	Ar	Ar	Ar + H2	1st : O2	
			Ar + O2	2nd: Ar+H2	
Key process	解離	解離	活化+解離	活化燃燒+解離	

Bonding (Wire Selection)



Process Focus

- FAB (Free Air Ball) Hardness
 - □ Soft wire (4N) for weak bond pad structure
 - Hard wire (AuPd/ 2N) for small BPP application
- Break load/ Elongation
 - □ Good for looping form & molding wire sweep by high "BL"
 - Good performance for stitch pull by low" BL" with high "EL"
 - Reduce cap. growth up by low "BL"

Reliability

- Good for reliability by AuPd wire
 - Intermatecillic growth is slow

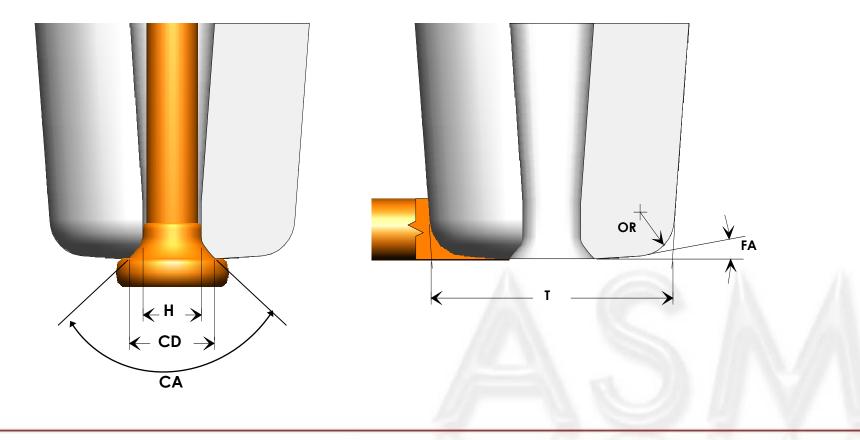
BPP (um)	BPO (um)	Max. Wire Length	Wire size	Finger Pitch
B.P.P.≧ 80	B.P.O.≧ 70	5334 um (210mil) <= MWL < 5588 um (220mil)	30um	
		5080 um (200mil) <= MWL< 5334 um (210mil)	30um	145 um min.
		MWL < 5080 um (200mil)	25um	140 um min.
70≦B.P.P.<80	60≦B.P.O.<70	5080 um (200mil) <= MWL< 5334 um (210mil)	25um	145 um min.
		MWL < 5080 um (200mil)	25um	140 um min.
60≦B.P.P.<70	50≦B.P.O.<60	4572 um (180mil) <= MWL< 5080 um (200mil)	23um	140 um min.
		MWL< 4572 um (180mil)	23um	135 um min.
55≦B.P.P.<60	45 <u>≤</u> B.P.O.<50	4064 um (160mil) <=MWL< 4572 um (180mil)	20um	135 um min.
		MWL< 4064 um (160mil)	20um	130 um min.
50≤B.P.P.<55	40 <u>≤</u> B.P.O.<45	3556um (140mil) <= MWL< 4064um (160mil)	18um	130 um min.
		MWL< 3556um (140mil)	18um	130 um min.

Process Affect on 1st bond

Hole (H)/ Chamfer Diameter (CD)/ Inner Chamfer Angle (ICA)

Process Affect on 2nd Bond

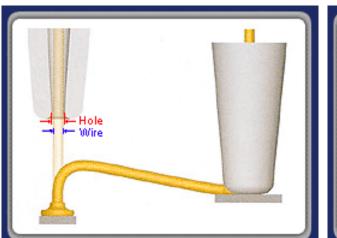
Tip (T) / Outside Radius (OR) / Face Angle (FA) / Chamfer Diameter (CD)

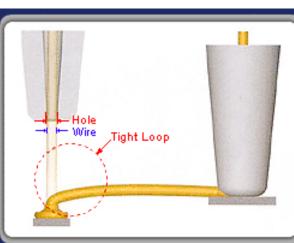


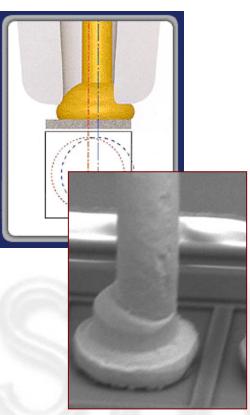


Hole Diameter (HD)

- Rule of thump
 - □ Hole Diameter = wire diameter + 0.2mil
 - Larger hole is better working for smoother wire stream ,but may fail to finely adjust the bond placement on the right place causing off-center on pad





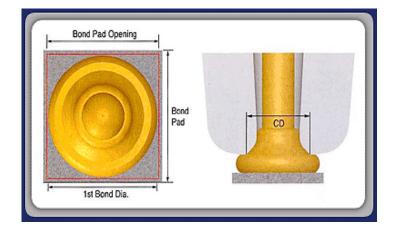


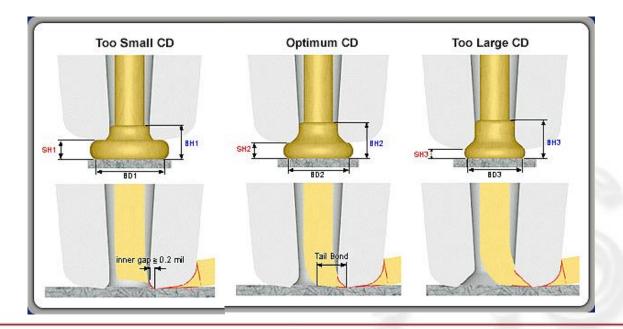




Chamfer Diameter (CD)

- Rule of thump
 - □ Chamfer Diameter = Ball size 6~8µm
 - Effect on 1st Bond
 - Affect 1st bond ball deformation
 - □ Effect on 2nd Bond
 - CD too small cause short tail
 - Improve stitch strength, increase CD reduce hole diameter

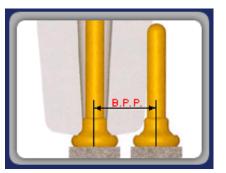


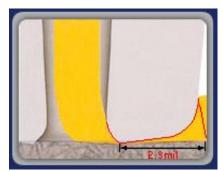




Tip (T)

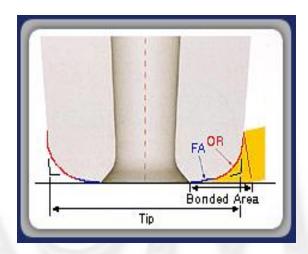
- Rule of thump
 - □ Tip Diameter = BPP *1.3
 - Small TD: 2nd bond may be weak
 - Large TD: Can see the cap interference with 1st bond & looping





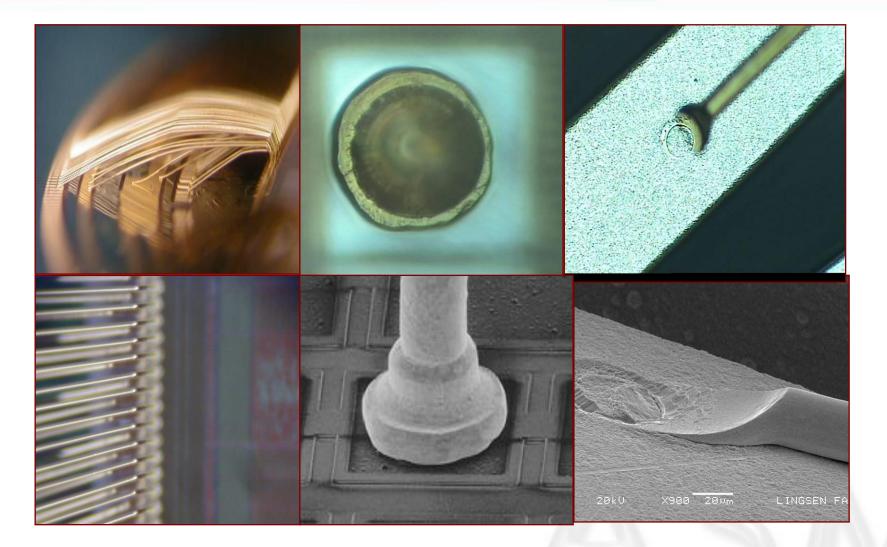
Face Angle (FA)/ Outside Radius (OR)

- Control the wedge width and wedge thickness
- Small FA will result in sharp corners
 - Cause heel crack on wedge
 - Higher FA and smaller OR leads to optimum wedge width
- Recommend OR: 3~ 5um , FA: 8~11 degree



Quality (Normal)





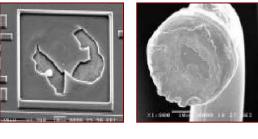
AL Peeling

- Process
 - Reduce bond power, and increase bond force
 - Increase ball size
 - Reduce Cap. CD
 - Reduce impact on bond pad (reduce search speed)
 - Al coating process (review with wafer house)
- Hardware
 - Review if die floating

It is easy to cause NSOP when reduce bond power











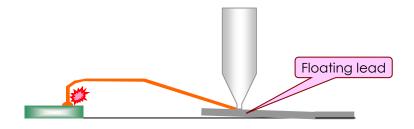
Neck crack

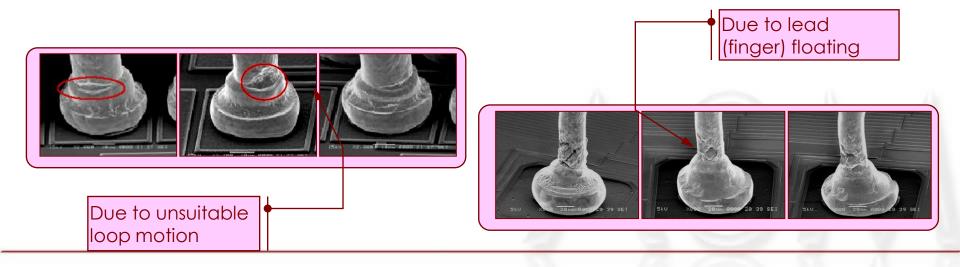




To check lead (finger) if floating

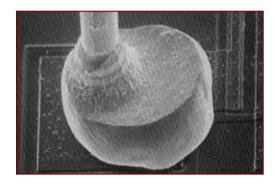
- Wire clamp opening too small
- Process
 - Larger reverse motion on looping
 - Reduce RD/ RDA, raise RH
 - 2nd power too large to cause neck crack
 - Reduce 2nd power/ increase bond force
 - EFO current too large





Golf Ball/ Abnormal ball size/ Miss ball

- Hardware
 - Clean wire spool/ wire path/ air tensioner (Cause wire contamination)
 - Clean/ calibration wire clamp due to unstable wire clamp motion open/ close
 - E-torch damage to cause abnormal sparking
 - Tail bond unstable to cause tail bent
 - Finger contamination/ floating
 - Check "fire level" if with in STD setting
 - **EFO** box or cable connection problem





- 1st bond power too larger
- Raise EFO current
 - It is 35mA for 0.8mil WD for 38um ball size
- 1st bond search high too low
- Cap. hole size too larger
- Tail too short
- □ Tip of tail length swing away from E-torch

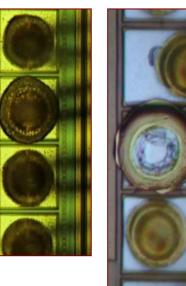


Smash Ball

- Solution (Hardware)
 - Check bond force sensor (Z driver BD) if damage
 - Calibration / Check wire clamp due to noise
 - Check if die floating
 - Check FAB size if too small
 - EFO Torch tip setting no good
 - BQM board not calibrated.
 - Dirty Torch Tip
 - Inconsistent Die Thickness / Die Height
 - EFO Box Problem
 - Air diffuser too large

Process

- Raise search high/ reduce search speed
- Unsuitable search parameter ("LW" too small)
- Initial force too larger
- □ To raise power "raise time"
- □ 2~3 ms power delay on 1st bond
- Reduce base power







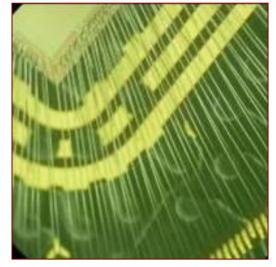
Quality (Looping)

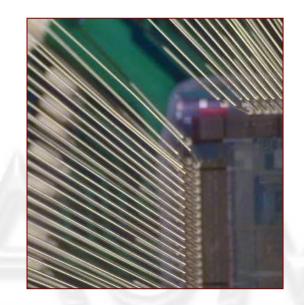
Wire sweep/ sagging

- Solution (Hardware)
 - Check wire path if smooth
 - Check/ calibration wire clamp
 - Check if index to cause wire sweep/ sagging
- Solution (Process)
 - Reduce 2nd bond power
 - □ Fine tune loop parameter "LC"
 - More reverse on 1st kink

Loop base bent

- Solution (Hardware)
 - Check wire clamp
 - Check/ calibration wire clamp
- Solution (Process)
 - Fine tune loop parameter
 - Reduce RDA (negative is better)
 - Check if unsuitable cap tip size
 - Check if unsuitable "EL" on wire







Quality (Looping)

Snake wire

- Solution (Hardware)
 - Check/ calibration wire clamp force
- Solution (Process)
 - Add scrub/ bond smooth motion on 2nd bond
 - Check wire clamp profile if with in STD setting
 - Enable "Tail break motion"
 - Increase Tail power
 - Provide tail power in advance stage
 - Reduce the speed for "tail to fire level"











~End~